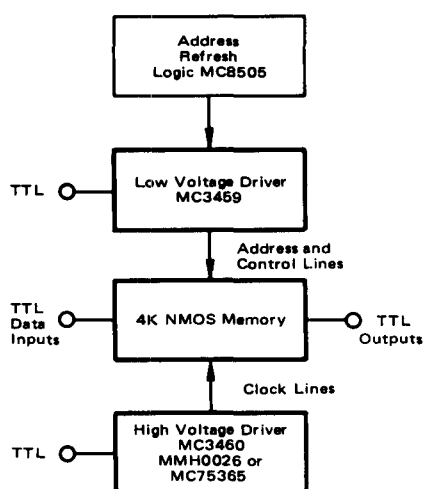
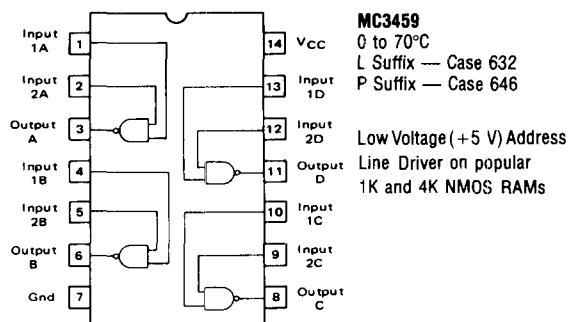


V_{OH} ④ $I_{OH} = -100 \mu A$ Volts Min.	V_{OL} ④ $I_{OL} = 10 mA$ Volts Max.	t_{DLH} ④ $C_L = 390 pF$ ns Max.
$V_{CC} - 3.0$	0.2	24

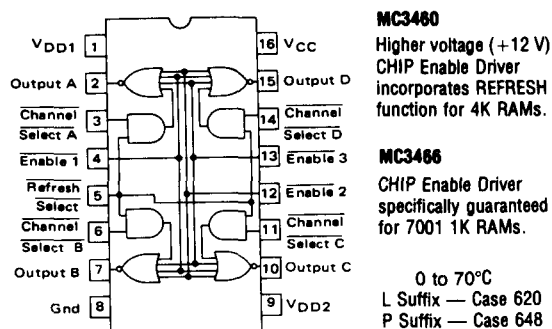
4K NMOS MEMORIES For TTL Systems . . .



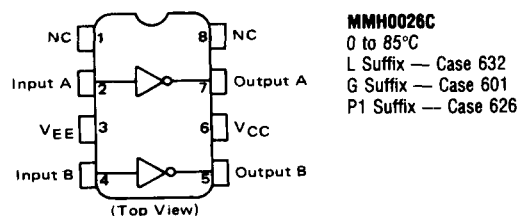
Today's 4K NMOS RAMs provide economical mass storage in popular TTL logic systems.



V_{OH} ④ $I_{OH} = -2.0 mA$ Volts Min.	V_{OL} ④ $I_{OL} = 80 mA$ Volts Max.	t_{PLH} ④ $C_L = 360 pF$ ns Max.
2.4	0.7	26



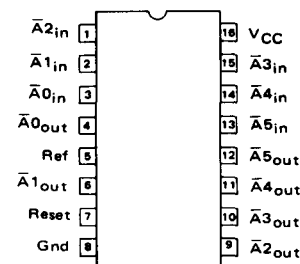
V_{OH} ④ $I_{OH} = -2.0 mA$ Volts Min.	V_{OL} ④ $I_{OL} = 40 mA$ Volts Max.	t_{DLH} ④ $C_L = 480 pF$ ns Max.
$V_{DD} - 1.0$	0.55	23



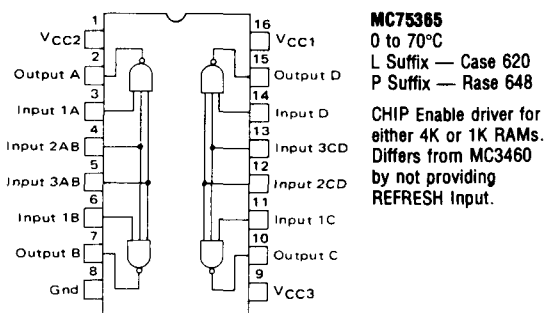
Pin Connections for P1 Package

Drivers for extremely heavy capacitive loading (to 1000 pF).

V_{OL} ④ $V_1 - V_{EE} = 0.4 V$ Volts Min.	V_{OL} ④ $V_1 - V_{EE} = 2.5 V$ Volts Max.	t_{PHL} ④ $C_L = 1000 pF$ ns Max.
$V_{CC} - 1.0$	$V_{EE} + 0.5 V$	12



V_{OH} ④ $I_O = -300 \mu A$ Volts Min.	V_{OL} ④ $I_O = 3.2 mA$ Volts Max.	$t_{PD} (ADDRESS)$ ns Max.	$t_{PD} (REFRESH)$ ns Max.
2.4	0.5	80	145



V_{OH} ④ $I_{OH} = -100 \mu A$ Volts Min.	V_{OL} ④ $I_{OL} = 10 mA$ Volts Max.	t_{DLH} ④ $C_L = 200 pF$ ns Max.
$V_{CC} - 0.3$	0.3	20